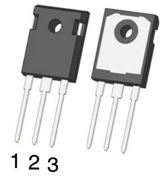
Silicon Carbide (SiC) Cascode JFET - EliteSiC, Power N-Channel, TO247-3, 750 V, 18 mohm

UJ4C075018K3S



TO247-3 15.90x20.96x5.03, 5.44P
CASE 340AK

Description

The UJ4C075018K3S is a 750 V, 18 mΩ G4 SiC FET. It is based on unique 'cascode' circuit configuration, in which a normally-on SiC JFET is co-packaged with a Si MOSFET to produce a normally-off SiC FET device. The device's standard gate-drive characteristics allows for a true "drop-in replacement" to Si IGBTs, Si FETs, SiC MOSFETs or Si super-junction devices. Available in the TO247-3 package, this device exhibits ultra-low gate charge and exceptional reverse recovery characteristics, making it ideal for switching inductive loads and any application requiring standard gate drive.

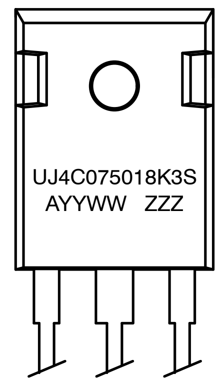
Features

- On-Resistance $R_{DS(on)}$: 18 mΩ (typ)
- Operating Temperature: 175 °C (max)
- Excellent Reverse Recovery: Q_{rr} = 102 nC
- Low Body Diode V_{FSD}: 1.14 V
- Low Gate Charge: Q_G = 37.8 nC
- Threshold Voltage $V_{G(th)}$: 4.8 V (typ) Allowing 0 to 15 V Drive
- Low Intrinsic Capacitance
- ESD Protected: HBM Class 2 and CDM Class C3
- This Device is Pb-Free, Halogen Free and is RoHS Compliant

Typical Applications

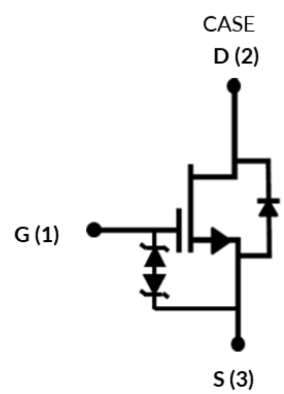
- EV Charging
- PV Inverters
- Switch Mode Power Supplies
- Power Factor Correction Modules
- Motor Drives
- Induction Heating

MARKING DIAGRAM



UJ4C075018K3S	= Specific Device Code
A	= Assembly Location
YY	= Year
WW	= Work Week
ZZZ	= Lot ID

PIN CONNECTIONS



ORDERING INFORMATION

See detailed ordering and shipping information on page 11 of this data sheet.

MAXIMUM RATINGS

Parameter	Symbol	Test Conditions	Value	Unit
Drain-Source Voltage	V_{DS}		750	V
Gate-Source Voltage	V_{GS}	DC	−20 to +20	V
		AC (f > 1 Hz)	−25 to +25	V
Continuous Drain Current (Note 1)	I_D	T_C = 25 °C	81	A
		T_C = 100 °C	60	
Pulsed Drain Current (Note 2)	I_{DM}	T_C = 25 °C	205	A
Single Pulsed Avalanche Energy (Note 3)	E_{AS}	L = 15 mH, I_{AS} = 3.6 A	97.2	mJ
Power Dissipation	P_{tot}	T_C = 25 °C	385	W
Maximum Junction Temperature	$T_{J,max}$		175	°C
Operating and Storage Temperature	T_J, T_{STG}		−55 to 175	°C
Max. Lead Temperature for Soldering, 1/8” from Case for 5 Seconds	T_L		250	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Limited by $T_{J,max.}$
2. Pulse width t_p limited by $T_{J,max.}$
3. Starting T_J = 25 °C.

THERMAL CHARACTERISTICS

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$		–	0.3	0.39	°C/W

ELECTRICAL CHARACTERISTICS (T_J = 25 °C unless otherwise specified)

Parameter	Symbol	Test Conditions		Min	Typ	Max	Unit
TYPICAL PERFORMANCE – STATIC							
Drain-Source Breakdown Voltage	BV_{DS}	V_{GS} = 0 V, I_D = 1 mA		750	–	–	V
Total Drain Leakage Current	I_{DSS}	V_{DS} = 750 V, V_{GS} = 0 V, T_J = 25 °C		–	1.3	125	μA
		V_{DS} = 750 V, V_{GS} = 0 V, T_J = 175°C		–	20	–	
Total Gate Leakage Current	I_{GSS}	V_{DS} = 0 V, V_{GS} = −20 V / + 20 V		–	4.7	±20	μA
Drain-Source On-resistance	$R_{DS(on)}$	V_{GS} = 12 V, I_D = 50 A	T_J = 25 °C	–	18	23	mΩ
			T_J = 125 °C	–	31	–	
			T_J = 175 °C	–	41	–	
Gate Threshold Voltage	$V_{G(th)}$	V_{DS} = 5 V, I_D = 10 mA		4	4.8	6	V
Gate Resistance	R_G	f = 1 MHz, open drain		–	4.5	–	Ω
TYPICAL PERFORMANCE – REVERSE DIODE							
Diode Continuous Forward Current (Note 4)	I_S	T_C = 25 °C		–	–	81	A
Diode Pulse Current (Note 5)	$I_{S,pulse}$	T_C = 25 °C		–	–	205	A
Forward Voltage	V_{FSD}	V_{GS} = 0 V, I_S = 20 A, T_J = 25 °C		–	1.14	1.46	V
		V_{GS} = 0 V, I_S = 20 A, T_J = 175 °C		–	1.35	–	
Reverse Recovery Charge	Q_{rr}	V_{DS} = 400 V, I_S = 50 A, V_{GS} = 0 V, R_{G_EXT} = 50 Ω, di/dt = 1400 A/μs, T_J = 25 °C		–	102	–	nC
Reverse Recovery Time	t_{rr}			–	25	–	ns
Reverse Recovery Charge	Q_{rr}	V_{DS} = 400 V, I_S = 50 A, V_{GS} = 0 V, R_{G_EXT} = 50 Ω, di/dt = 1400 A/μs, T_J = 150 °C		–	109	–	nC
Reverse Recovery Time	t_{rr}			–	27	–	ns

ELECTRICAL CHARACTERISTICS (T_J = 25 °C unless otherwise specified) (continued)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
TYPICAL PERFORMANCE – DYNAMIC						
Input Capacitance	C_{iss}	V_{DS} = 400 V, V_{GS} = 0 V, f = 100 kHz	–	1414	–	pF
Output Capacitance	C_{oss}		–	118	–	
Reverse Transfer Capacitance	C_{rss}		–	2	–	
Effective Output Capacitance, Energy Related	$C_{oss(er)}$	V_{DS} = 0 V to 400 V, V_{GS} = 0 V	–	150	–	pF
Effective Output Capacitance, Time Related	$C_{oss(tr)}$		–	280	–	pF
C_{OSS} Stored Energy	E_{oss}	V_{DS} = 400 V, V_{GS} = 0 V	–	12	–	μJ
Total Gate Charge	Q_G	V_{DS} = 400 V, I_D = 50 A, V_{GS} = 0 V to 15 V	–	37.8	–	nC
Gate-Drain Charge	Q_{GD}		–	8	–	
Gate-Source Charge	Q_{GS}		–	11.8		
Turn-on Delay Time	$t_{d(on)}$	V_{DS} = 400 V, I_D = 50 A, Gate Driver = 0 V, to +15 V, Turn-on $R_{G,EXT}$ = 1 Ω, Turn-off $R_{G,EXT}$ = 50 Ω, Inductive Load, FWD: same device with V_{GS} = 0 V and R_G = 50 Ω, T_J = 25 °C (Note 6)	–	13	–	ns
Rise Time	t_r		–	56	–	
Turn-off Delay Time	$t_{d(off)}$		–	139	–	
Fall Time	t_f		–	21	–	
Turn-on Energy	E_{ON}		–	615	–	μJ
Turn-off Energy	E_{OFF}		–	518	–	
Total Switching Energy	E_{TOTAL}		–	1133	–	
Turn-on Delay Time	$t_{d(on)}$	V_{DS} = 400 V, I_D = 50 A, Gate Driver = 0 V, to +15 V, Turn-on $R_{G,EXT}$ = 1 Ω, Turn-off $R_{G,EXT}$ = 50 Ω, Inductive Load, FWD: same device with V_{GS} = 0 V and R_G = 50 Ω, T_J = 150 °C (Note 6)	–	13	–	ns
Rise Time	t_r		–	62	–	
Turn-off Delay Time	$t_{d(off)}$		–	147	–	
Fall Time	t_f		–	22	–	
Turn-on Energy	E_{ON}		–	670	–	μJ
Turn-off Energy	E_{OFF}		–	573	–	
Total Switching Energy	E_{TOTAL}		–	1243	–	
Turn-on Delay Time	$t_{d(on)}$	V_{DS} = 400 V, I_D = 50 A, Gate Driver = 0 V, to +15 V, $R_{G,EXT}$ = 1 Ω, Inductive Load, FWD: same device with V_{GS} = 0 V and R_G = 1 Ω, RC snubber: R_{S1} = 10 Ω and C_{S1} = 300 pF, T_J = 25 °C (Note 7)	–	13	–	ns
Rise Time	t_r		–	61	–	
Turn-off Delay Time	$t_{d(off)}$		–	33	–	
Fall Time	t_f		–	17	–	
Turn-on Energy Including R_S Energy	E_{ON}		–	696	–	μJ
Turn-off Energy Including R_S Energy	E_{OFF}		–	217	–	
Total Switching Energy	E_{TOTAL}		–	913	–	
Snubber R_S Energy During Turn-on	E_{RS_ON}		–	4	–	
Snubber R_S Energy During Turn-off	E_{RS_OFF}		–	8	–	

ELECTRICAL CHARACTERISTICS (T_J = 25 °C unless otherwise specified) (continued)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
TYPICAL PERFORMANCE – DYNAMIC						
Turn-on Delay Time	$t_{d(on)}$	V_{DS} = 400 V, I_D = 50 A, Gate Driver = 0 V, to +15 V, $R_{G,EXT}$ = 1 Ω, Inductive Load, FWD: same device with V_{GS} = 0 V and R_G = 1 Ω, RC snubber: R_{S1} = 10 Ω and C_{S1} = 300 pF, T_J = 150 °C (Note 7)	–	15	–	ns
Rise Time	t_r		–	64	–	
Turn-off Delay Time	$t_{d(off)}$		–	36	–	
Fall Time	t_f		–	18	–	
Turn-on Energy Including R_S Energy	E_{ON}		–	744	–	μJ
Turn-off Energy Including R_S Energy	E_{OFF}		–	229	–	
Total Switching Energy	E_{TOTAL}		–	973	–	
Snubber R_S Energy During Turn-on	E_{RS_ON}		–	4	–	
Snubber R_S Energy During Turn-off	E_{RS_OFF}		–	8	–	
Turn-on Delay Time	$t_{d(on)}$	V_{DS} = 400 V, I_D = 50 A, Gate Driver = 0 V, to +15 V, Turn-on $R_{G,EXT}$ = 1 Ω, Turn-off $R_{G,EXT}$ = 50 Ω, Inductive Load, FWD: UJ3D06530TS T_J = 25 °C (Note 8)	–	14	–	ns
Rise Time	t_r		–	54	–	
Turn-off Delay Time	$t_{d(off)}$		–	139	–	
Fall Time	t_f		–	21	–	
Turn-on Energy	E_{ON}		–	619	–	μJ
Turn-off Energy	E_{OFF}		–	549	–	
Total Switching Energy	E_{TOTAL}		–	1168	–	
Turn-on Delay Time	$t_{d(on)}$	V_{DS} = 400 V, I_D = 50 A, Gate Driver = 0 V, to +15 V, Turn-on $R_{G,EXT}$ = 1 Ω, Turn-off $R_{G,EXT}$ = 50 Ω, Inductive Load, FWD: UJ3D06530TS T_J = 150 °C (Note 8)	–	14	–	ns
Rise Time	t_r		–	59	–	
Turn-off Delay Time	$t_{d(off)}$		–	140	–	
Fall Time	t_f		–	24	–	
Turn-on Energy	E_{ON}		–	665	–	μJ
Turn-off Energy	E_{OFF}		–	611	–	
Total Switching Energy	E_{TOTAL}		–	1276	–	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Limited by $T_{J,max}$.
5. Pulse width t_p limited by $T_{J,max}$.
6. Measured with the half-bridge mode switching test circuit in Figure 29.
7. Measured with the half-bridge mode switching test circuit in Figure 31.
8. Measured with the chopper mode switching test circuit in Figure 30.

TYPICAL PERFORMANCE DIAGRAMS

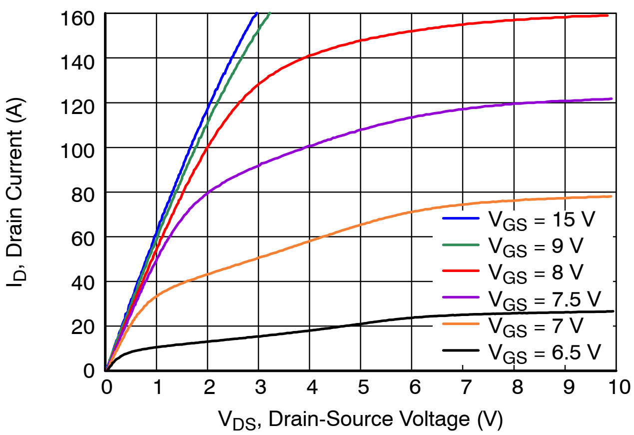


Figure 1. Typical Output Characteristics at T_J = −55 °C, t_p < 250 μs

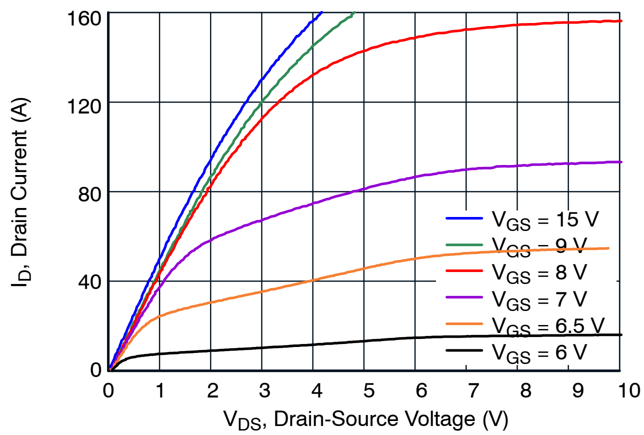


Figure 2. Typical Output Characteristics at T_J = 25 °C, t_p < 250 μs

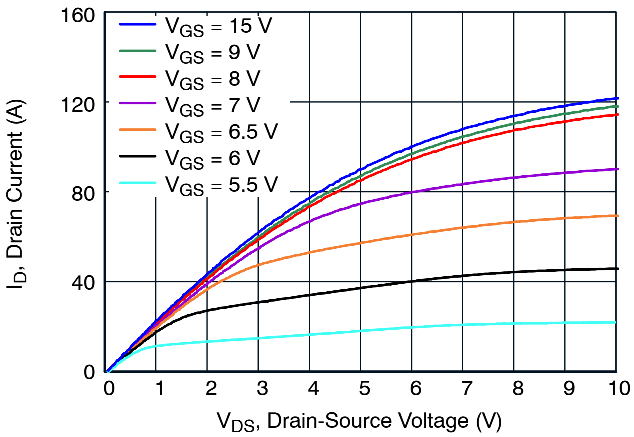


Figure 3. Typical Output Characteristics at T_J = 175 °C, t_p < 250 μs

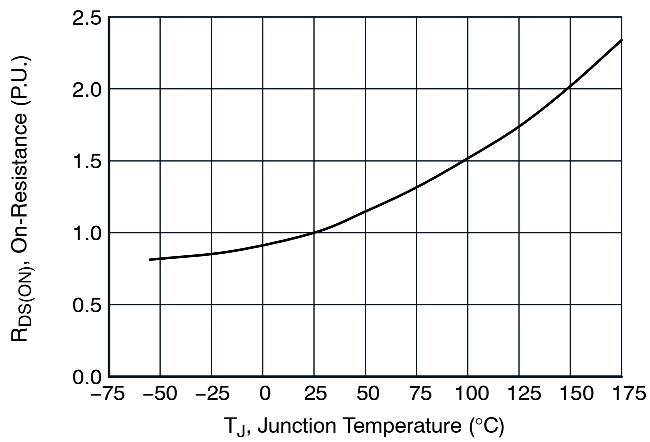


Figure 4. Normalized On-Resistance vs. Temperature at V_{GS} = 12 V and I_D = 50 A

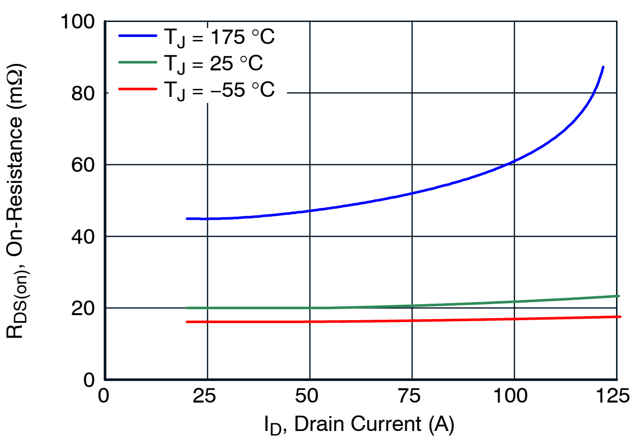


Figure 5. Typical Drain-Source On-Resistances at V_{GS} = 12 V

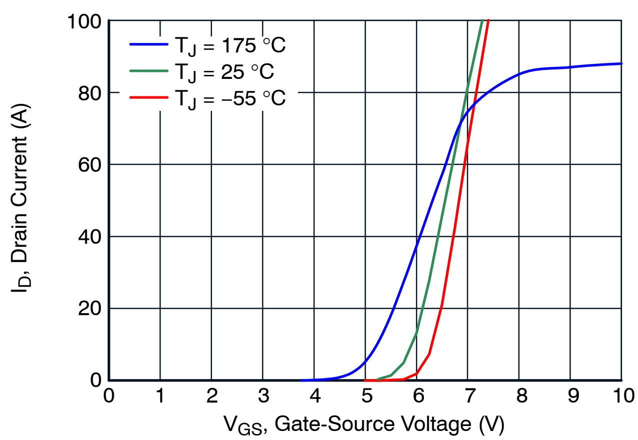


Figure 6. Typical Transfer Characteristics at V_{DS} = 5 V

TYPICAL PERFORMANCE DIAGRAMS (continued)

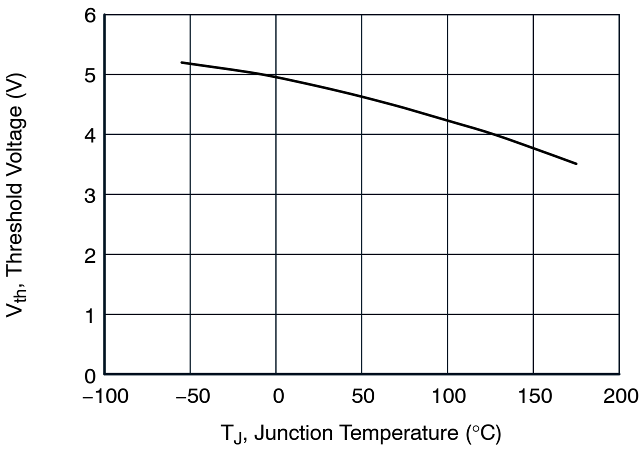


Figure 7. Threshold Voltage vs. Junction Temperature at V_{DS} = 5 V and I_D = 10 mA

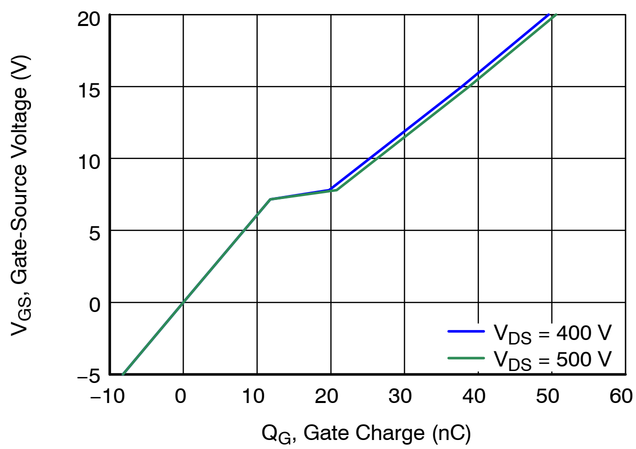


Figure 8. Typical Gate Charge at I_D = 50 A

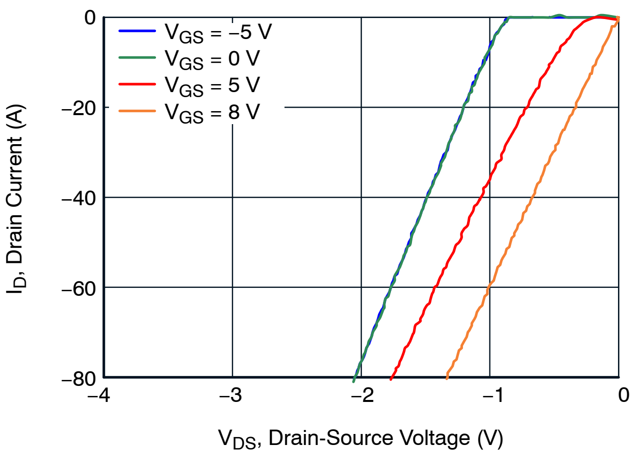


Figure 9. 3rd Quadrant Characteristics at T_J = −55 °C

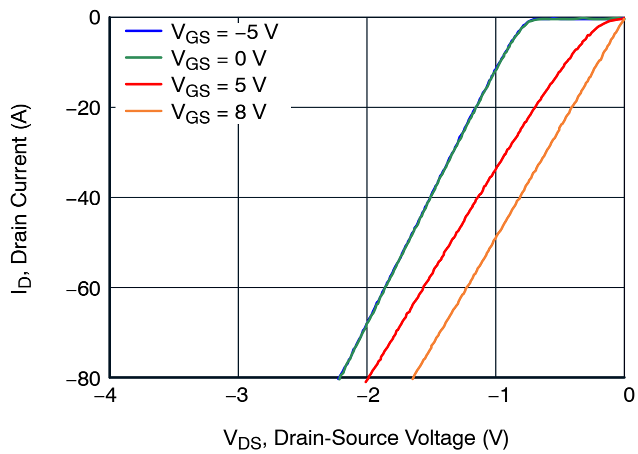


Figure 10. 3rd Quadrant Characteristics at T_J = 25 °C

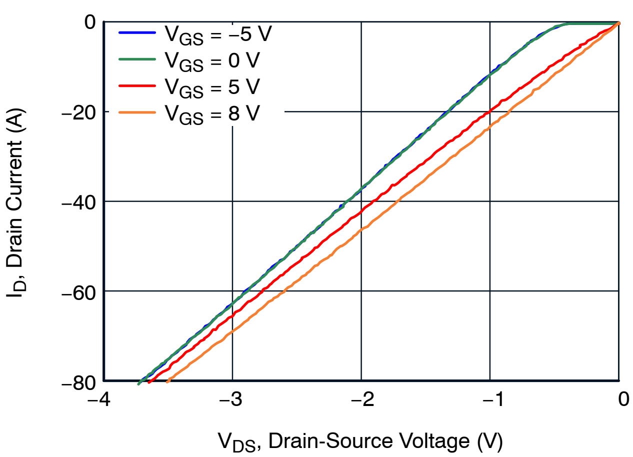


Figure 11. 3rd Quadrant Characteristics at T_J = 175 °C

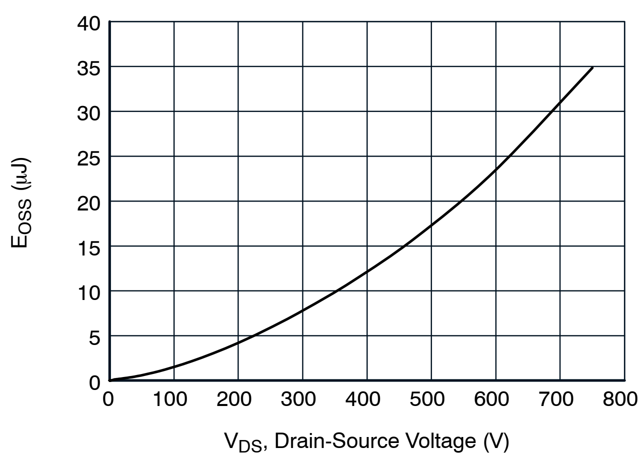


Figure 12. Typical Stored Energy in C_{OSS} at V_{GS} = 0 V

TYPICAL PERFORMANCE DIAGRAMS (continued)

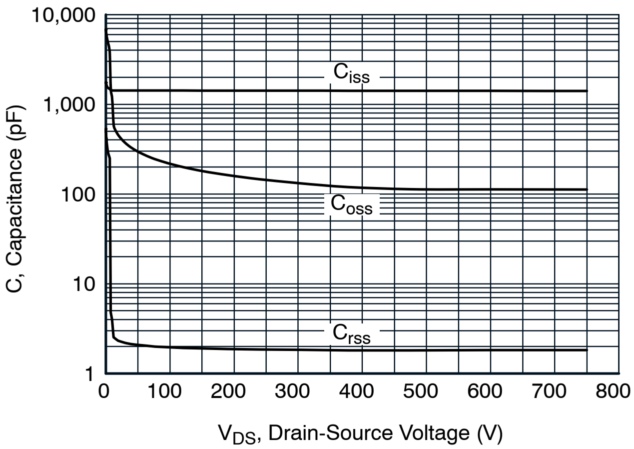


Figure 13. Typical Capacitances at f = 100 kHz and V_{GS} = 0 V

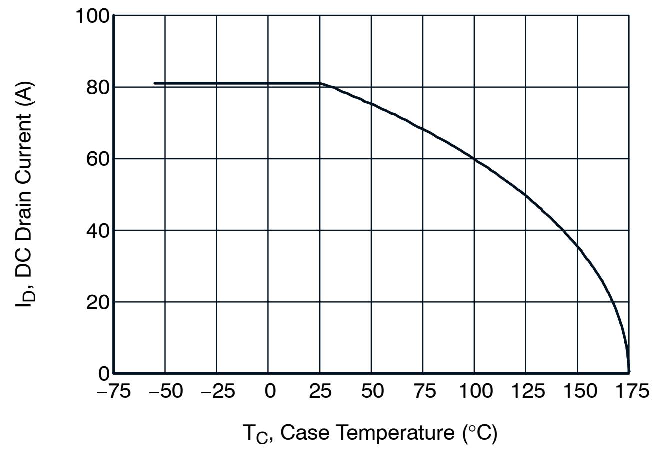


Figure 14. DC Drain Current Derating

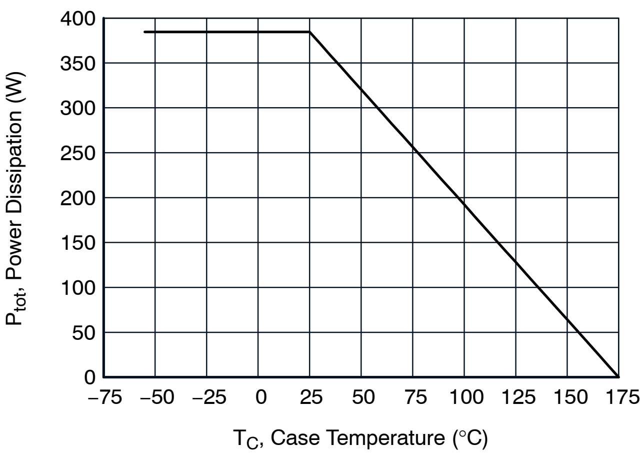
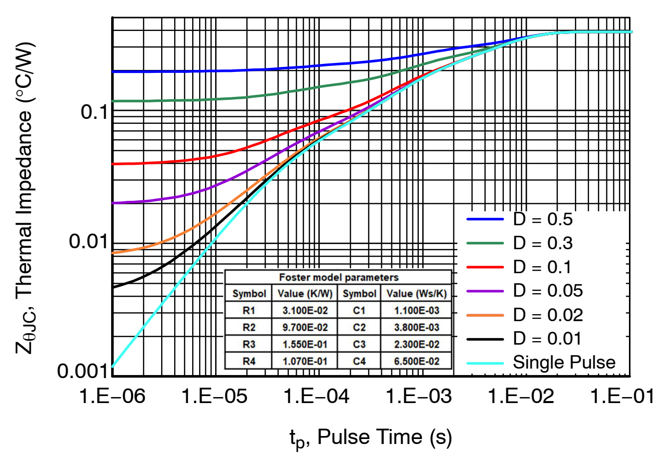


Figure 15. Total Power Dissipation



Foster model parameters			
Symbol	Value (K/W)	Symbol	Value (Ws/K)
R1	3.100E-02	C1	1.100E-03
R2	9.700E-02	C2	3.800E-03
R3	1.550E-01	C3	2.300E-02
R4	1.070E-01	C4	6.500E-02

Figure 16. Maximum Transient Thermal Impedance

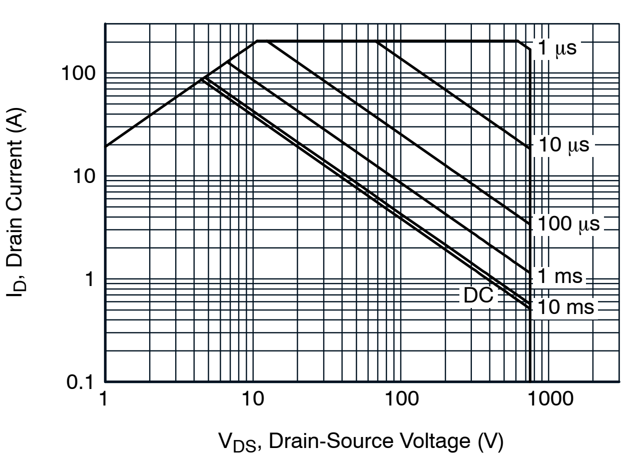


Figure 17. Safe Operation Area at T_C = 25 °C, D = 0, Parameter t_p

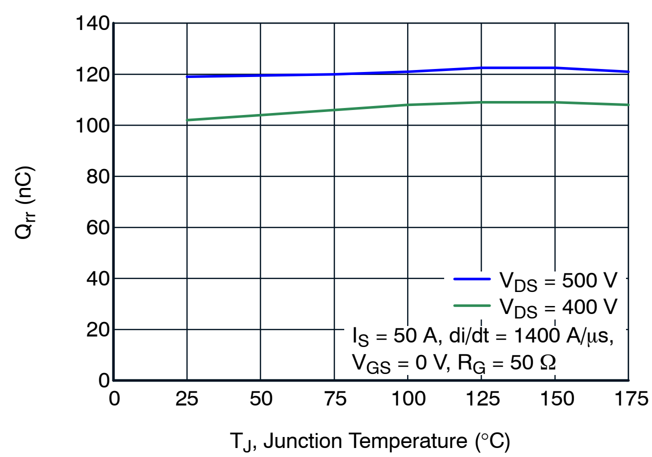


Figure 18. Reverse Recovery Charge Q_{rr} vs. Junction Temperature

TYPICAL PERFORMANCE DIAGRAMS (continued)

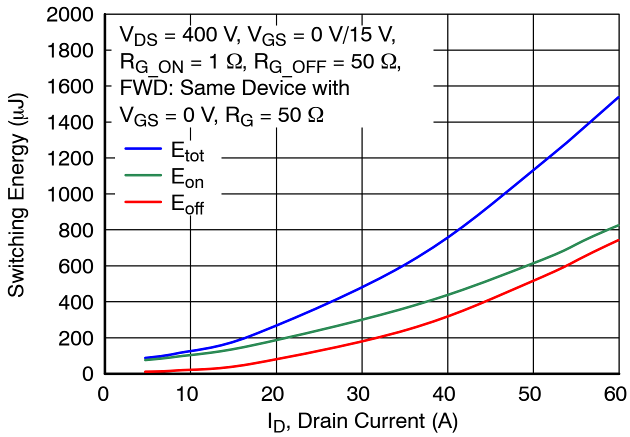


Figure 19. Clamped Inductive Switching Energy vs. Drain Current at V_{DS} = 400 V and T_J = 25 °C

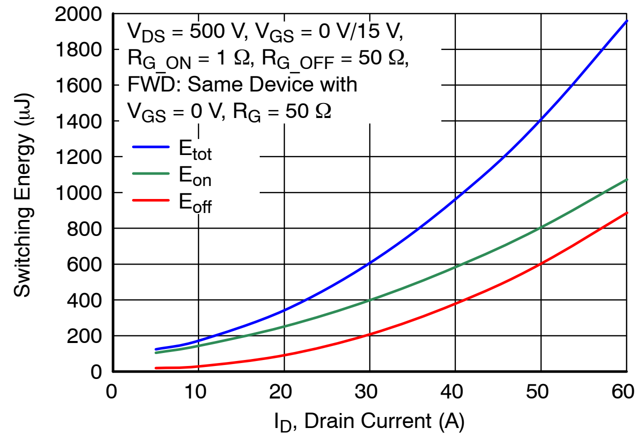


Figure 20. Clamped Inductive Switching Energy vs. Drain Current at V_{DS} = 500 V and T_J = 25 °C

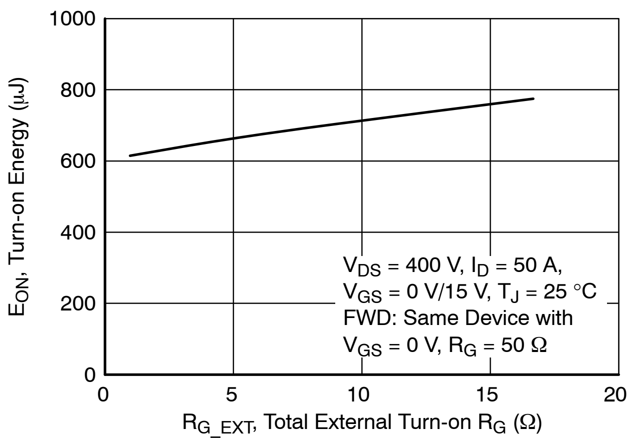


Figure 21. Clamped Inductive Switching Turn-On Energy vs. Total External Turn-on R_G

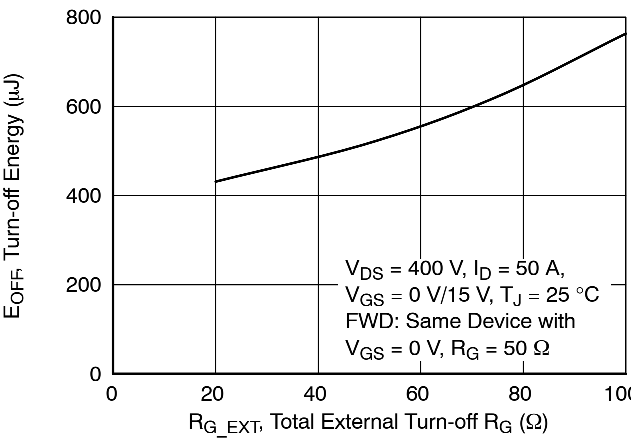


Figure 22. Clamped Inductive Switching Turn-Off Energy vs. Total External Turn-off R_G

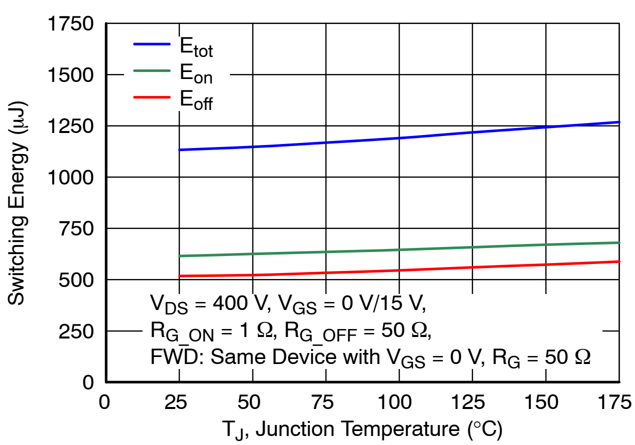


Figure 23. Clamped Inductive Switching Energy vs. Junction Temperature at V_{DS} = 400 V and I_D = 50 A

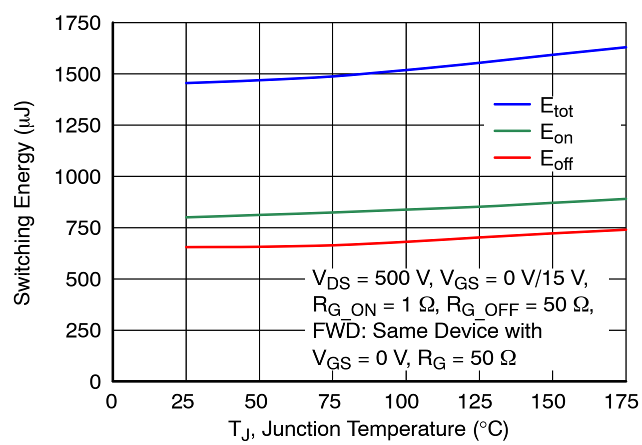


Figure 24. Clamped Inductive Switching Energy vs. Junction Temperature at V_{DS} = 500 V and I_D = 50 A

TYPICAL PERFORMANCE DIAGRAMS (continued)

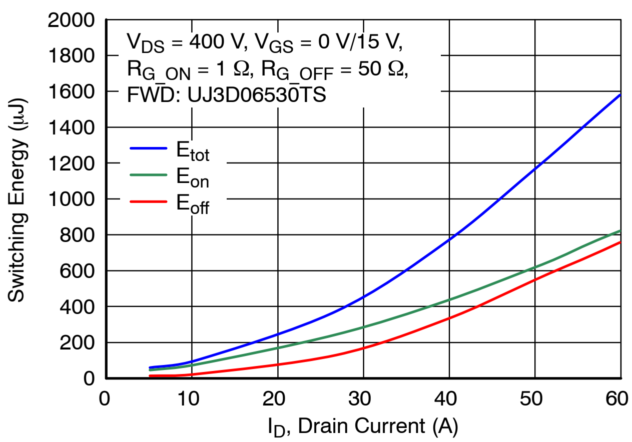


Figure 25. Clamped Inductive Switching Energy vs. Drain Current at V_{DS} = 400 V and T_J = 25 °C

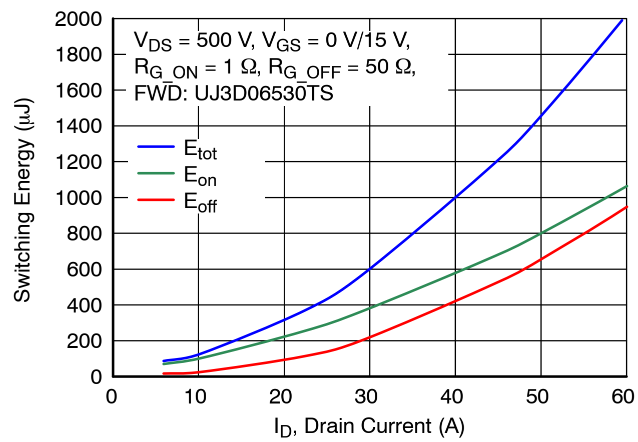


Figure 26. Clamped Inductive Switching Energy vs. Drain Current at V_{DS} = 500 V and T_J = 25 °C

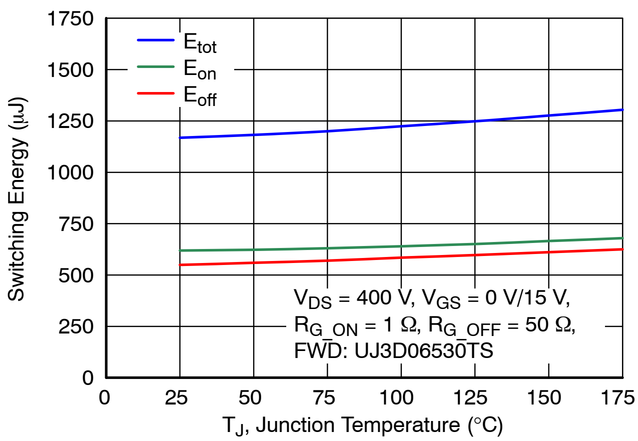


Figure 27. Clamped Inductive Switching Energy vs. Junction Temperature at V_{DS} = 400 V and I_D = 50 A

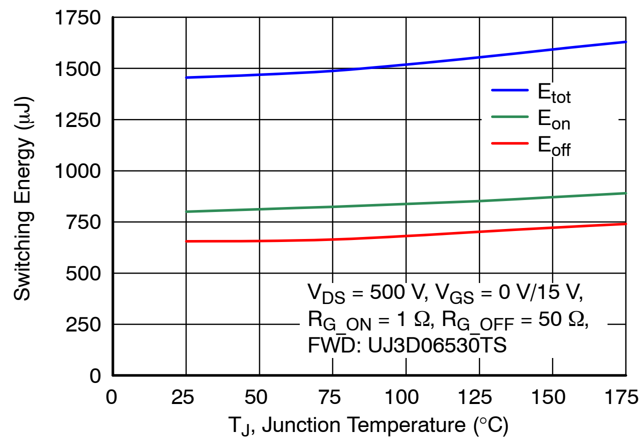


Figure 28. Clamped Inductive Switching Energy vs. Junction Temperature at V_{DS} = 500 V and I_D = 50 A

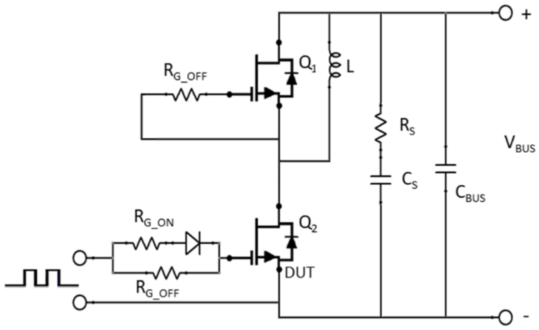


Figure 29. Schematic of the Half-Bridge Mode Switching Test Circuit. Note, a Bus RC Snubber (R_S = 2.5 Ω, C_S = 100 nF) is Used to Reduce the Power Loop High Frequency Oscillations

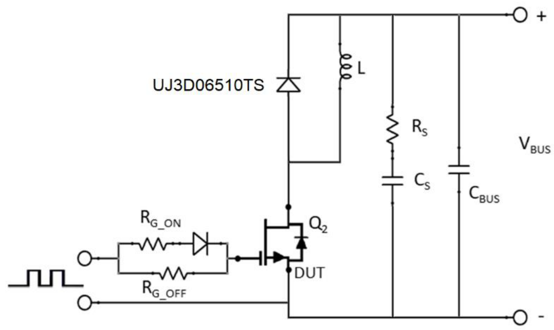


Figure 30. Schematic of the Chopper Mode Switching Test Circuit. Note, a Bus RC Snubber (R_S = 2.5 Ω, C_S = 100 nF) is Used to Reduce the Power Loop High Frequency Oscillations

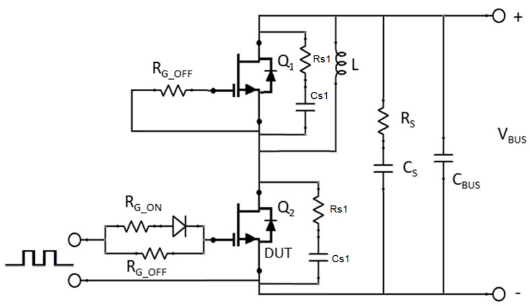


Figure 31. Schematic of the Half-Bridge Mode Switching Test Circuit with device RC Snubber (R_{S1} = 10 Ω, C_{S1} = 300 pF) and a Bus RC Snubber (R_S = 2.5 Ω, C_S = 100 nF)

APPLICATIONS INFORMATION

SiC FETs are enhancement-mode power switches formed by a high-voltage SiC depletion-mode JFET and a low-voltage silicon MOSFET connected in series. The silicon MOSFET serves as the control unit while the SiC JFET provides high voltage blocking in the off state. This combination of devices in a single package provides compatibility with standard gate drivers and offers superior performance in terms of low on-resistance ($R_{DS(on)}$), output capacitance (C_{oss}), gate charge (Q_G), and reverse recovery charge (Q_{rr}) leading to low conduction and switching losses. The SiC FETs also provide excellent reverse conduction capability eliminating the need for an external anti-parallel diode.

Like other high performance power switches, proper PCB layout design to minimize circuit parasitics is strongly recommended due to the high dv/dt and di/dt rates. An external gate resistor is recommended when the FET is working in the diode mode in order to achieve the optimum reverse recovery performance. For more information on SiC FET operation, see www.onsemi.com.

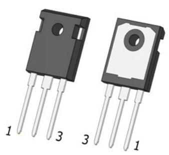
A snubber circuit with a small $R_{(G)}$, or gate resistor, provides better EMI suppression with higher efficiency compared to using a high $R_{(G)}$ value. There is no extra gate delay time when using the snubber circuitry, and a small $R_{(G)}$ will better control both the turn-off $V_{(DS)}$ peak spike and ringing duration, while a high $R_{(G)}$ will damp the peak spike but result in a longer delay time. In addition, the total switching loss when using a snubber circuit is less than using high $R_{(G)}$, while greatly reducing $E_{(OFF)}$ from mid-to-full load range with only a small increase in $E_{(ON)}$. Efficiency will therefore improve with higher load current. For more information on how a snubber circuit will improve overall system performance, visit the **onsemi** website at www.onsemi.com.

ORDERING INFORMATION

Part Number	Marking	Package	Shipping
UJ4C075018K3S	UJ4C075018K3S	TO247-3 15.90x20.96x5.03, 5.44P (Pb-Free, Halogen Free)	600 Units / Tube

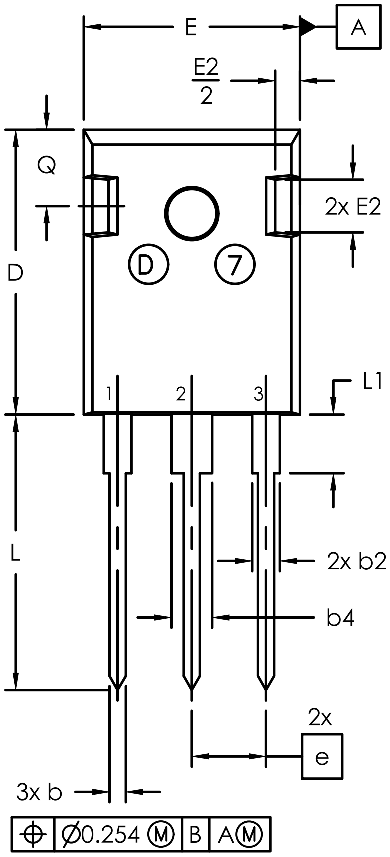
REVISION HISTORY

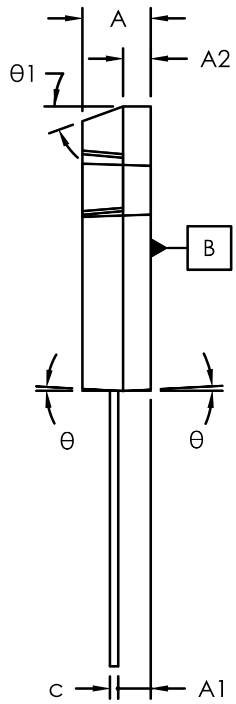
Revision	Description of Changes	Date
B	Acquired the original Qorvo JFET Division Data Sheet and updated the main document title to comply with **onsemi** standards for SiC products.	1/15/2025
2	Converted the Data Sheet to **onsemi** format.	5/27/2025

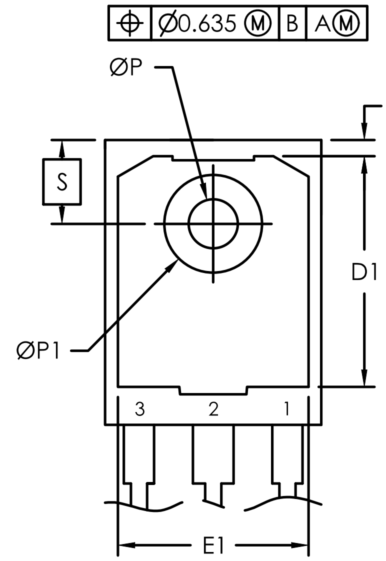


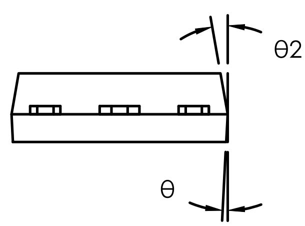
TO247−3 15.90x20.96x5.03, 5.44P
CASE 340AK
ISSUE B

DATE 14 APR 2025









SYM	millimeters		
	MIN	NOM	MAX
A	4.70	5.03	5.31
A1	2.21	2.40	2.59
A2	1.50	2.03	2.49
b	0.99	1.20	1.40
b2	1.65	2.03	2.39
b4	2.59	3.00	3.43
c	0.38	0.60	0.89
D	20.70	20.96	21.46
D1	13.08	–	–
D2	0.51	1.19	1.35
E	15.49	15.90	16.26
e	5.44 BSC		
E1	13.00	13.30	13.60
E2	3.43	3.89	5.20
L	19.62	20.27	20.32
L1	–	–	4.50
ØP	3.40	3.60	3.80
ØP1	7.06	7.19	7.39
Q	5.38	5.62	6.20
S	6.15 BSC		
θ	3°		
θ1	20°		
θ2	10°		

NOTE:
1. Dimensioning and tolerancing as per ASME Y14.5 - 2018
2. Controlling dimension : millimeters
3. Package Outline in compliance with JEDEC standard var. AD.
4. Dimensions D & E does not include mold flash.
5. ØP to have max draft angle of 1.7° to the top with max. hole diameter of 3.91mm.

DOCUMENT NUMBER:	98AON88794E	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	TO247−3 15.90x20.96x5.03, 5.44P	PAGE 1 OF 1

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:
Technical Library: www.onsemi.com/design/resources/technical−documentation
onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support
For additional information, please contact your local Sales Representative at www.onsemi.com/support/sales

◊